

Abstract

A semiconductor apparatus includes a semiconductor chip **61** including a power semiconductor device using a wide band gap semiconductor, base materials **62** and **63**, first and second intermediate members **65** and **68a**, a heat conducting member **66**, a radiation fin **67**, and an encapsulating material **68** for encapsulating the semiconductor chip **61**, the first and second intermediate member **65** and **68a** and the heat conducting member **66**.
5 The tips of the base materials **62** and **63** work respectively as external connection terminals **62a** and **63a**. The second intermediate member **68a** is made of a material with lower heat conductivity than the first intermediate member **65**, and a contact area with the
10 semiconductor chip **61** is larger in the second intermediate member **68a** than in the first intermediate member.